Per-Ake Nilsson

List of Publications by Year
in descending order

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51 papers	1,627 citations	331259 21 h-index	288905 40 g-index
51 all docs	51 docs citations	51 times ranked	963 citing authors

#	Article	IF	Citations
1	0.3-14 and 16-28 GHz Wide-Bandwidth Cryogenic MMIC Low-Noise Amplifiers. IEEE Transactions on Microwave Theory and Techniques, 2018, , 1-10.	2.9	27
2	Dependence of noise temperature on physical temperature for cryogenic low-noise amplifiers. Journal of Astronomical Telescopes, Instruments, and Systems, 2017, 3, 014003.	1.0	11
3	Two-Finger InP HEMT Design for Stable Cryogenic Operation of Ultra-Low-Noise Ka- and Q-Band LNAs. IEEE Transactions on Microwave Theory and Techniques, 2017, 65, 5171-5180.	2.9	21
4	Two-finger InP HEMT design for stable cryogenic operation of ultra-low-noise Ka-band LNAs. , 2017, , .		2
5	Nanochannel diodes based on InAs/Al80Ga20Sb heterostructures: Fabrication and zero-bias detector properties. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2015, 33, 021207.	0.6	1
6	Cryogenic Kink Effect in InP pHEMTs: A Pulsed Measurements Study. IEEE Transactions on Electron Devices, 2015, 62, 532-537.	1.6	11
7	Suppression of Parasitic Substrate Modes in Multilayer Integrated Circuits. IEEE Transactions on Electromagnetic Compatibility, 2015, 57, 591-594.	1.4	7
8	DC, RF and noise performance of InAs/AlSb HEMTs with in situ CVD SiNx-film for early-protection against oxidation. Solid-State Electronics, 2013, 87, 85-89.	0.8	8
9	Terahertz detection in zero-bias InAs self-switching diodes at room temperature. Applied Physics Letters, 2013, 103, .	1.5	41
10	Characterization and Modeling of Cryogenic Ultralow-Noise InP HEMTs. IEEE Transactions on Electron Devices, 2013, 60, 206-212.	1.6	38
11	Cryogenic Broadband Ultra-Low-Noise MMIC LNAs for Radio Astronomy Applications. IEEE Transactions on Microwave Theory and Techniques, 2013, 61, 871-877.	2.9	76
12	Cryogenic Performance of Low-Noise InP HEMTs: A Monte Carlo Study. IEEE Transactions on Electron Devices, 2013, 60, 1625-1631.	1.6	9
13	True planar InAs/AlSb HEMTs with ion-implantation technique for low-power cryogenic applications. Solid-State Electronics, 2013, 79, 268-273.	0.8	2
14	Fabrication and DC characterization of InAs/AlSb self-switching diodes. , 2012, , .		4
15	Cryogenic InAs/AlSb HEMT Wideband Low-Noise IF Amplifier for Ultra-Low-Power Applications. IEEE Microwave and Wireless Components Letters, 2012, 22, 144-146.	2.0	65
16	Planar InAs/AlSb HEMTs With Ion-Implanted Isolation. IEEE Electron Device Letters, 2012, 33, 510-512.	2.2	13
17	Ultralow-Power Cryogenic InP HEMT With Minimum Noise Temperature of 1 K at 6 GHz. IEEE Electron Device Letters, 2012, 33, 664-666.	2.2	86
18	InAs/AlSb HEMTs for cryogenic LNAs at ultra-low power dissipation. Solid-State Electronics, 2011, 64, 47-53.	0.8	15

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19	Transient Simulation of Microwave SiC MESFETs With Improved Trap Models. IEEE Transactions on Electron Devices, 2010, 57, 729-732.	1.6	17
20	Anisotropic transport properties in InAs/AlSb heterostructures. Applied Physics Letters, 2010, 97, .	1.5	20
21	Thermal Study of the High-Frequency Noise in GaN HEMTs. IEEE Transactions on Microwave Theory and Techniques, 2009, 57, 19-26.	2.9	50
22	Influence of Field Plates and Surface Traps on Microwave Silicon Carbide MESFETs. IEEE Transactions on Electron Devices, 2008, 55, 1875-1879.	1.6	11
23	A Single-Ended Resistive X-Band AlGaN/GaN HEMT MMIC Mixer. IEEE Transactions on Microwave Theory and Techniques, 2008, 56, 2201-2206.	2.9	25
24	An AlGaN/GaN HEMT-Based Microstrip MMIC Process for Advanced Transceiver Design. IEEE Transactions on Microwave Theory and Techniques, 2008, 56, 1827-1833.	2.9	49
25	SiC Varactors for Dynamic Load Modulation of High Power Amplifiers. IEEE Electron Device Letters, 2008, 29, 728-730.	2.2	15
26	Electro-thermal simulations of a microwave 4H-SiC MESFET on high purity semi-insulating substrate. Solid-State Electronics, 2007, 51, 1144-1152.	0.8	17
27	Design and Fabrication of 4H-SiC RF MOSFETs. IEEE Transactions on Electron Devices, 2007, 54, 3138-3145.	1.6	10
28	Fabrication and characterization of field-plated buried-gate SiC MESFETs. IEEE Electron Device Letters, 2006, 27, 573-575.	2.2	66
29	An SiC MESFET-Based MMIC Process. IEEE Transactions on Microwave Theory and Techniques, 2006, 54, 4072-4078.	2.9	34
30	A highly linear double balanced Schottky diode S-band mixer. IEEE Microwave and Wireless Components Letters, 2006, 16, 336-338.	2.0	17
31	High field-effect mobility in n-channel Si face 4H-SiC MOSFETs with gate oxide grown on aluminum ion-implanted material. IEEE Electron Device Letters, 2005, 26, 96-98.	2.2	51
32	High field effect mobility in Si face 4H-SiC MOSFET transistors. Electronics Letters, 2004, 40, 508.	0.5	30
33	Low excess flux noise in YBa/sub 2/Cu/sub 3/O/sub 7-x/ dc SQUIDs cooled in static magnetic fields. IEEE Transactions on Applied Superconductivity, 1997, 7, 2772-2775.	1.1	5
34	Reduction of 1/f noise in highâ€Tc dc superconducting quantum interference devices cooled in an ambient magnetic field. Applied Physics Letters, 1996, 69, 4099-4101.	1.5	98
35	Josephson flux-flow resonances in overdamped longYBa2Cu3O7grain-boundary junctions. Physical Review B, 1995, 51, 8684-8687.	1.1	38
36	Planarized patterning of Y-Ba-Cu-O thin films for multilayer technology. IEEE Transactions on Applied Superconductivity, 1995, 5, 1653-1656.	1.1	4

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37	Fluxâ€flow transistors based on long YBa2Cu3O7âˆ'Î´bicrystal grain boundary junctions. Applied Physics Letters, 1994, 64, 1153-1155.	1.5	45
38	Influence of inductance induced noise in an YBa2Cu3O7dcâ€SQUID at high operation temperatures. Applied Physics Letters, 1994, 64, 2445-2447.	1.5	9
39	Bicrystal junctions and superconducting quantum interference devices in YBa2Cu3O7thin films. Journal of Applied Physics, 1994, 75, 7972-7977.	1.1	21
40	Electromagnetic properties at the grain boundary interface of aYBa2Cu3O7âˆ'Î´bicrystal Josephson junction. Physical Review Letters, 1994, 72, 1260-1263.	2.9	123
41	Growth and properties of YBa2Cu3O7âˆ'x/(SrTiO3/PrGaO3)/YBa2Cu3O7âˆ'xtrilayers: Optimization of the insulation. Journal of Applied Physics, 1994, 75, 827-834.	1.1	10
42	Microstructure of an artificial grain boundary weak link in an YBa2Cu3O7âˆ'Ïƒ thin film grown on a (100)(110), [001]-tilt Y-ZrO2 bicrystal. Ultramicroscopy, 1993, 51, 239-246.	0.8	58
43	Elimination of pinholes in epitaxial thin film YBa2Cu3O7âˆ'x/SrTiO3/PrGaO3multilayers. Applied Physics Letters, 1993, 63, 1567-1569.	1.5	9
44	100 GHz oscillations on monolithic highTcchip. Applied Physics Letters, 1993, 62, 896-898.	1.5	9
45	Laserâ€deposited PrGaO3films on SrTiO3substrates and in YBa2Cu3O7/PrGaO3/YBa2Cu3O7trilayers. Applied Physics Letters, 1992, 61, 486-488.	1.5	17
46	Low 1/fnoise in YBa2Cu3O7dc SQUIDs on (Y)ZrO2bicrystal substrates. Applied Physics Letters, 1992, 61, 861-863.	1.5	31
47	Effects of substrate temperature on the microstructure of YBa2Cu3O7âˆ'Î´ films grown on (001) Yâ€ZrO2 substrates. Applied Physics Letters, 1992, 61, 723-725.	1.5	35
48	Properties of artificial grain boundary weak links grown on Y-ZrO2bicrystals. Superconductor Science and Technology, 1991, 4, 439-441.	1.8	13
49	High resolution patterning of high Tcsuperconducting thin films. Superconductor Science and Technology, 1991, 4, S112-S114.	1.8	5
50	High quality YBCO thin films - laser deposition, co-evaporation, and device fabrication. Physica Scripta, 1991, 44, 95-101.	1.2	4
51	Weak links and dc SQUIDS on artificial nonsymmetric grain boundaries in YBa2Cu3O7âˆ'Î´. Applied Physics Letters, 1991, 59, 3030-3032.	1.5	244